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Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP350/12	1200	1200	1400
KP350/14	1400	1400	1600
KP350/16	1600	1600	1760
KP350/18	1800	1800	1900

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

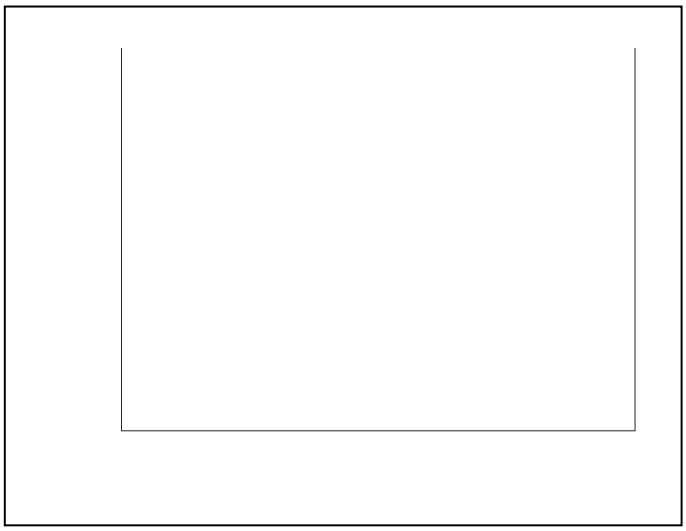
Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	2 mA 20 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μ

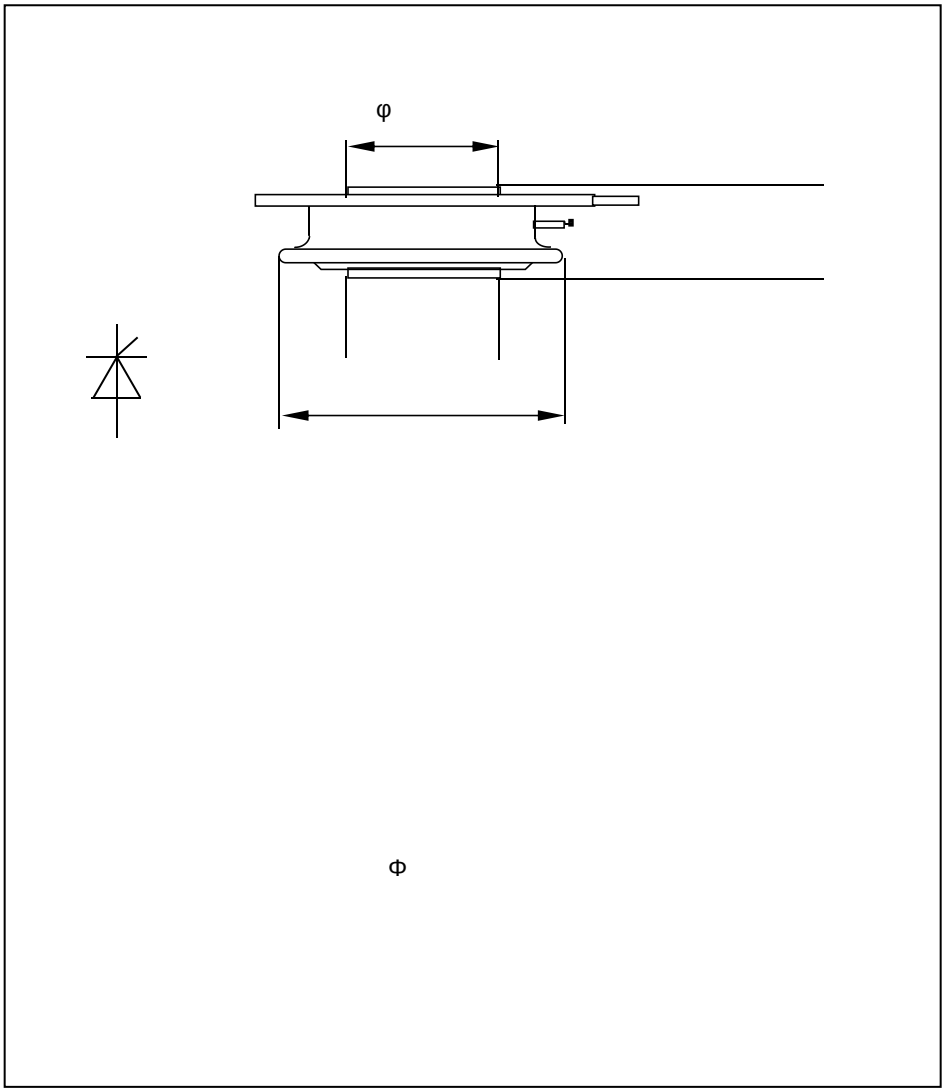
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		120		mA	V_D =12 V;R_L = 3 ohms;T_j = +25 °C
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D = 12 V;R_L = 3 ohms;T_j = +25 °C
Peak negative voltage	V_{GRM}		5		V	

Delay time	t_d		3.0	2.5	μs	I_{TM}=100A; V_D=67%V_{DRM} V_G=30V; R_G=10ohms; t_r=0.1μs; t_p=20μs
Turn-off time (with V_R = -5 V)	t_q			150	μs	I_{TM} =500A; di/dt =-10A/μs; V_R =100V; dv/dt=30V/μs ; V_D=67%V_{DRM};Tj=125
Reverse recovery charge	Q_{rr}				μC	I_{TM}=500A di/dt=-10A/μs; V_R=100V; T_j=125

Operating temperature	T_j	-40	+125		°C	
Storage temperature	T_{stg}	-40	+140		°C	
Thermal resistance - junction to case	$R_{\Theta (j-c)}$		0.08		°C/W	Double sided cooled
Thermal resistance - case to heatsink	$R_{\Theta (c-s)}$		0.02		°C/W	Double sided cooled
Mounting force	F	3.5	4.5	4	kN	
Weight	m			0.05	kg	

* Mounting surfaces smooth, flat and greased




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